

STGF5H60DF-VB Datasheet

600V Trench and Fieldstop IGBT

PRODUCT SUMMARY		
V_{CE} (V)	600	
I_C (A)	14 (TC=25 °C)	7 (TC=100 °C)
$V_{CE(sat)}$ (V)	1.6	
I_{CM} (A)	21	

FEATURES

- Very Low V_{CEsat}
- Low turn-off losses
- High speed switching
- Maximum junction temperature 175°C
- Ultra low gate charge (Q_g)
- Avalanche energy rated (UIS)



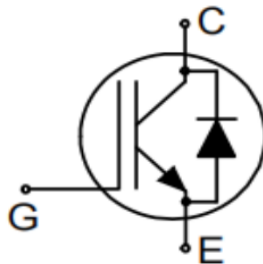
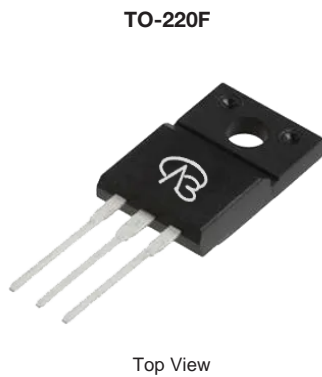
RoHS
COMPLIANT
HALOGEN
FREE

APPLICATIONS

- Telecommunications
 - Server and telecom power supplies
- Lighting
 - High-intensity discharge (HID)
 - Fluorescent ballast lighting
- Consumer and computing
 - ATX power supplies
- Industrial
 - Welding
 - Battery chargers
- Renewable energy
 - Solar (PV inverters)
- Switch mode power supplies (SMPS)

Package pin definition

- Pin1 G - Gate
- Pin2 C & backside - Collector
- Pin3 E - Emitter



ABSOLUTE MAXIMUM RATINGS ($T_C = 25\text{ °C}$, unless otherwise noted)			
PARAMETER	SYMBOL	LIMIT	UNIT
Collector-Emitter Voltage	V_{CE}	600	V
Gate-Emitter Voltage	V_{GE}	± 30	
Continuous Collector Current ($T_J = 150\text{ °C}$)	V_{GE} at 15 V	$T_C = 25\text{ °C}$	A
		$T_C = 100\text{ °C}$	
Pulsed Collector Current ^a	I_{CM}	21	
Diode Forward Current ^b	I_F	7	A
Maximum Power Dissipation	P_D	$T_C = 25\text{ °C}$	32
		$T_C = 100\text{ °C}$	11.0
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 to +175	°C
Short Circuit Withstand Time $T_C=150$	$V_{GE}= 15V, V_{CE} = 400V$	3	μs
Short Circuit Withstand Time $T_C=100$			
Soldering Recommendations (Peak Temperature) ^c	for 10 s	260	°C

Notes

- Repetitive rating; pulse width limited by maximum junction temperature.
- Current limited by maximum junction temperature.
- 1.6 mm from case.

THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	R_{thJA}	-	78	°C/W
Maximum Junction-to-Case	R_{thJC}	-	3.6	

SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Collector-Emitter Breakdown Voltage	BV_{CE}	$V_{GE} = 0\text{ V}, I_C = 250\text{ }\mu\text{A}$ $V_{GE} = 0\text{ V}, I_C = 1\text{ mA}$		600 600	- -	- -	V
Gate-Source Threshold Voltage (N)	$V_{GE(th)}$	$V_{CE} = V_{GE}, I_D = 250\text{ }\mu\text{A}$		4	5	6	V
Zero Gate Voltage Collector Current	I_{CES}	$V_{CE} = 600\text{ V}, V_{GE} = 0\text{ V}, T_J = 25\text{ }^\circ\text{C}$		-	1	20	μA
		$V_{CE} = 600\text{ V}, V_{GE} = 0\text{ V}, T_J = 150\text{ }^\circ\text{C}$		-	1000	-	μA
Gate-Emitter Leakage Current	I_{GES}	$V_{CE} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$		-	-	100	nA
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$V_{GE} = 7\text{ V}$	$I_C = 7\text{ A}$	-	1.7	2.1	V
Forward Transconductance	g_{fs}	$V_{CE} = 20\text{ V}, I_C = 7\text{ A}$		-	15	-	S
Dynamic							
Input Capacitance	C_{ies}	$V_{GE} = 0\text{ V}, V_{CE} = 25\text{ V},$ $f = 500\text{ KHz}$		-	930	-	pF
Output Capacitance	C_{oes}			-	30	-	
Reverse Transfer Capacitance	C_{res}			-	28	-	
Turn-on Energy	E_{on}	$V_{CE} = 400\text{ V}, V_{GE} = 0/15\text{V},$ $I_C = 7\text{ A}, R_g = 10\Omega$		-	0.32	-	nJ
Turn-off Energy	E_{off}			-	0.18	-	
Total Gate Charge	Q_g	$V_{GE} = 7\text{ V}$	$I_C = 7\text{ A}, V_{CE} = 400\text{ V}$	-	58	-	nC
Gate-Emitter Charge	Q_{ge}			-	11	-	
Gate to Collector Charge	Q_{gc}			-	19	-	
Turn-On Delay Time	$t_{d(on)}$	$V_{CE} = 400\text{ V}, V_{GE} = 0/15\text{V},$ $I_C = 7\text{ A}, R_g = 10\Omega$		-	15	-	ns
Rise Time	t_r			-	29	-	
Turn-Off Delay Time	$t_{d(off)}$			-	108	-	
Fall Time	t_f			-	39	-	
Internal emitter inductance measured 5 mm	L_E			-	13	-	nH
Diode Characteristics							
Diode Forward Current	I_F	IGBT symbol showing the integral reverse junction diode		-	-	7	A
Pulsed Diode Forward Current	I_{FM}			-	-	21	
Diode Forward Voltage	V_F	$I_F = 7\text{ A}$		-	1.68	2.0	V
Reverse Recovery Time	t_{rr}	$T_J = 25\text{ }^\circ\text{C}, I_F = 7\text{ A},$ $di_F/dt = 200\text{ A}/\mu\text{s}, V_R = 400\text{ V}$		-	60	-	ns
Reverse Recovery Charge	Q_{rr}			-	0.36	-	μC
Reverse Recovery Current	I_{RRM}			-	8	-	A

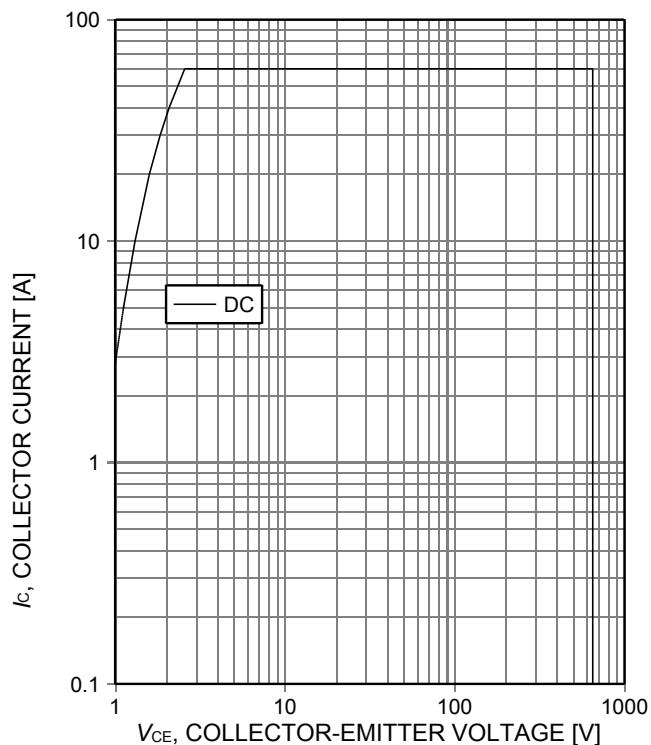


Figure 1. **Forward bias safe operating area**
($D=0$, $T_C=25^\circ\text{C}$, $T_{vj}\leq 175^\circ\text{C}$; $V_{GE}=15\text{V}$.
Recommended use at $V_{GE}\geq 7.5\text{V}$)

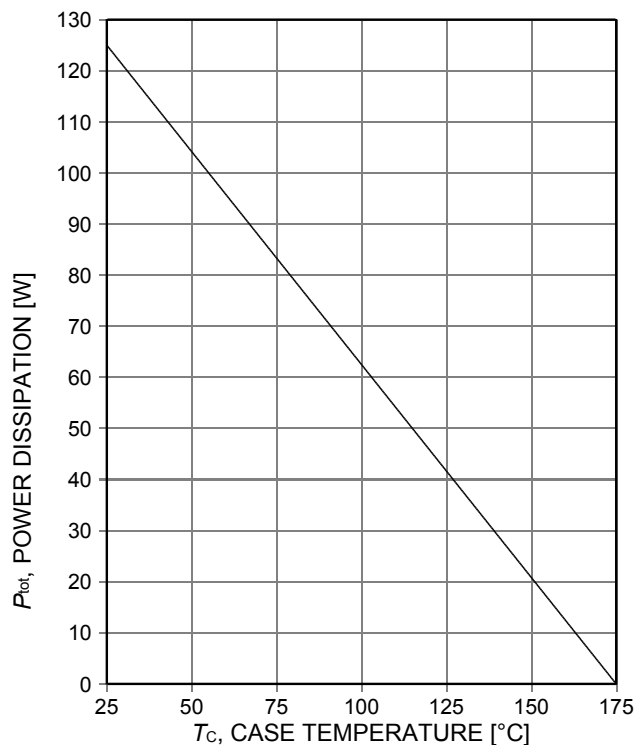


Figure 2. **Power dissipation as a function of case temperature**
($T_{vj}\leq 175^\circ\text{C}$)

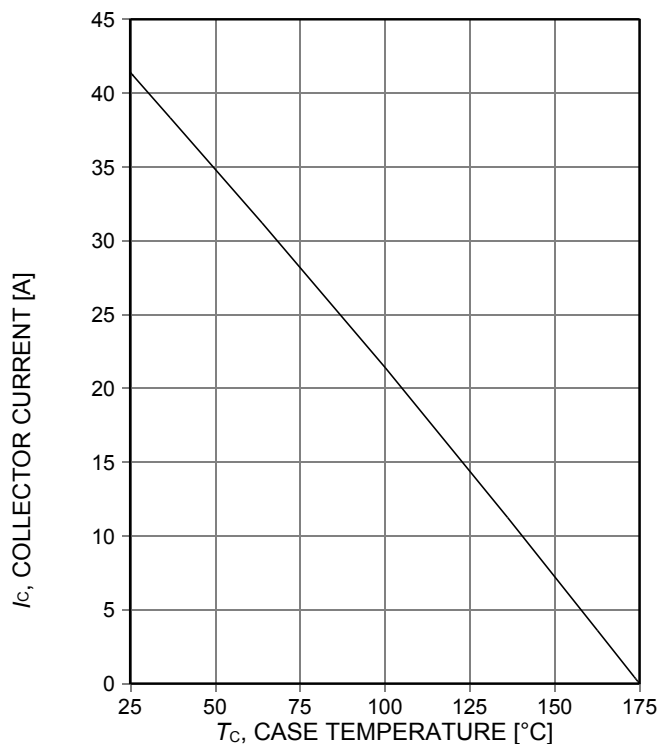


Figure 3. **Collector current as a function of case temperature**

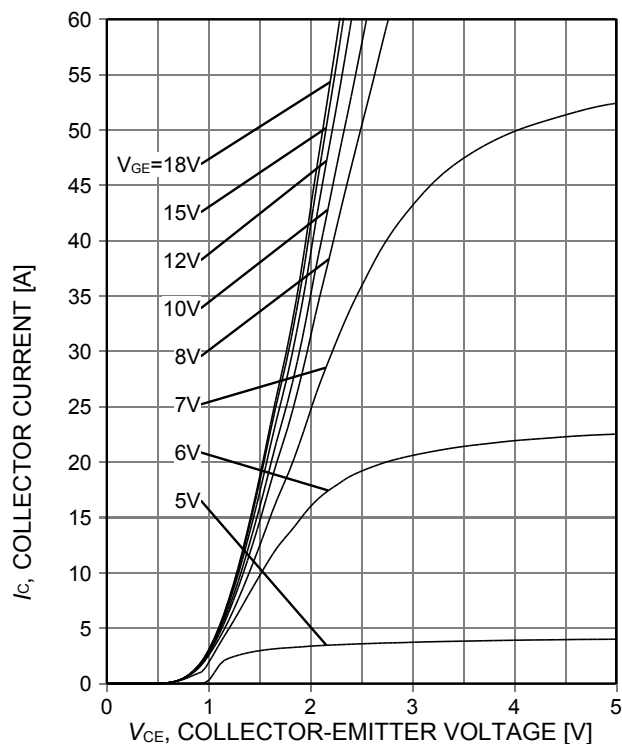


Figure 4. **Typical output characteristic**

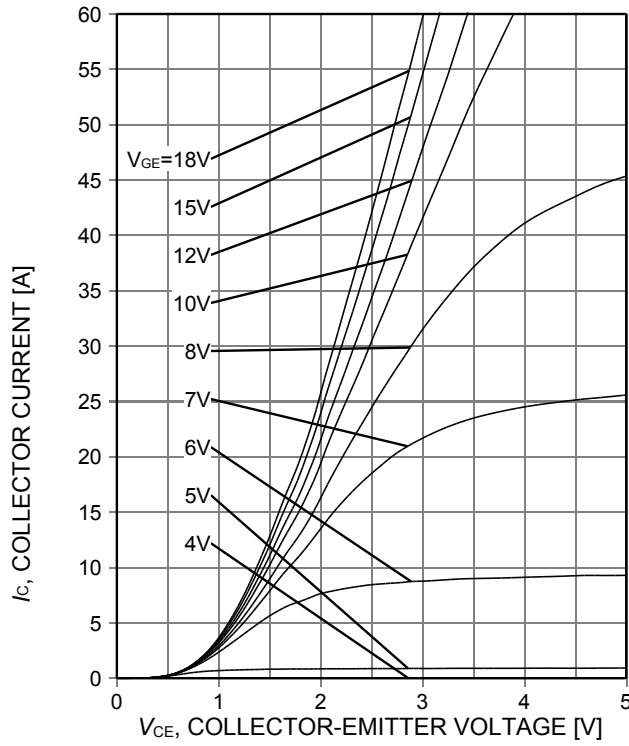


Figure 5. Typical output characteristic ($T_j=150^\circ\text{C}$)

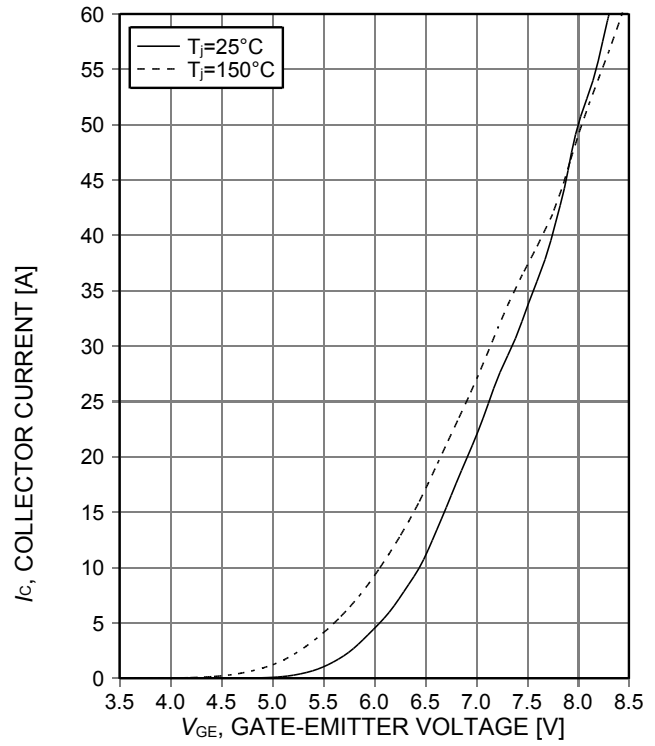


Figure 6. Typical transfer characteristic ($V_{CE}=20\text{V}$)

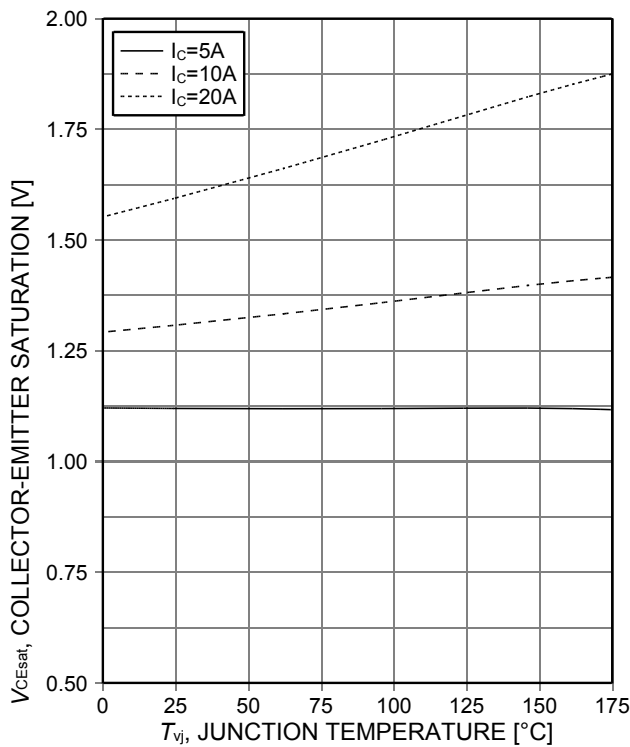


Figure 7. Typical collector-emitter saturation voltage as a function of junction temperature

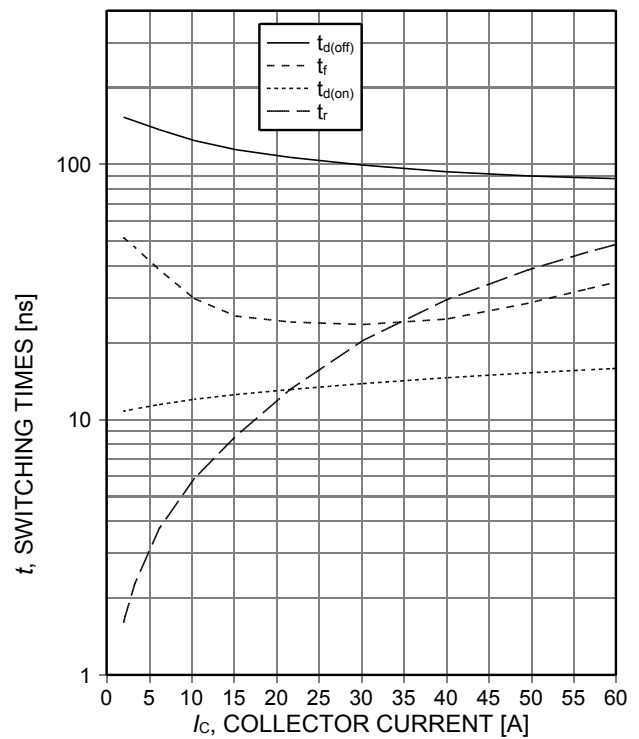


Figure 8. Typical switching times as a function of collector current

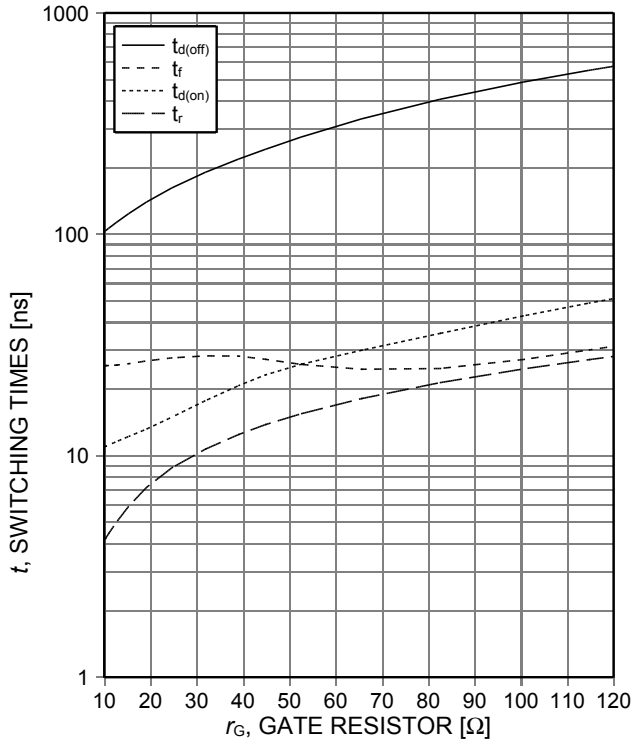


Figure 9. Typical switching times as a function of gate resistor

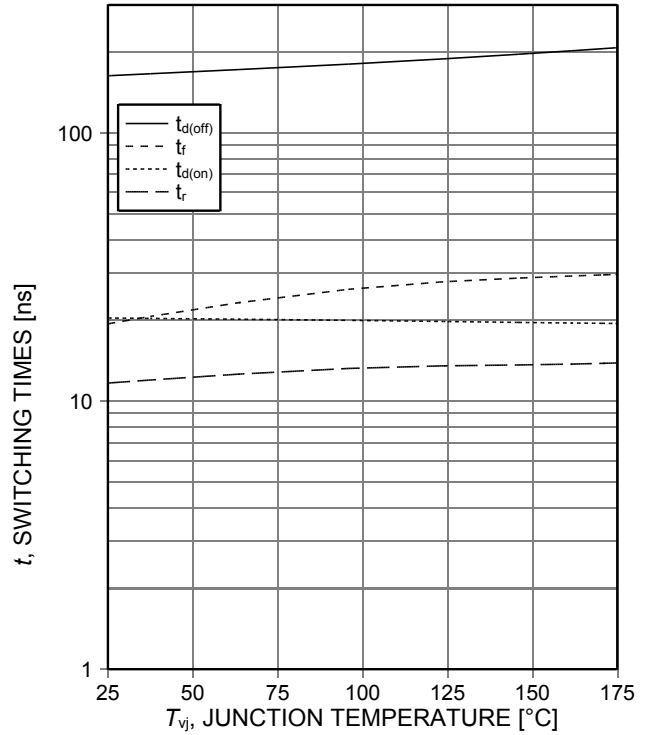


Figure 10. Typical switching times as a function of junction temperature

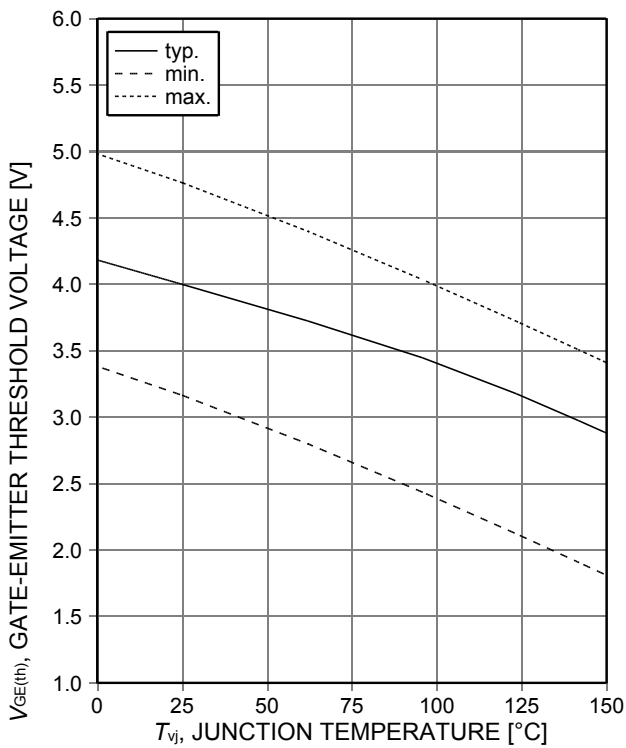


Figure 11. Gate-emitter threshold voltage as a function of junction temperature

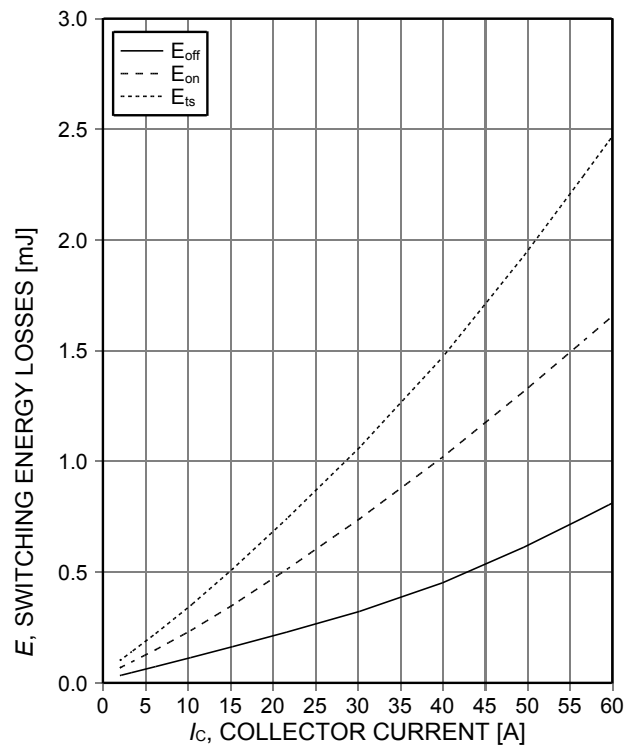


Figure 12. Typical switching energy losses as a function of collector current

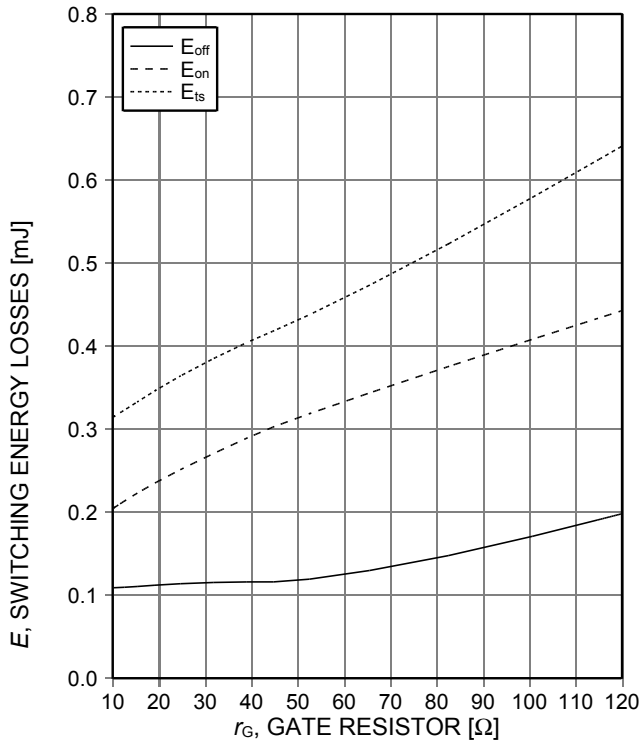


Figure 13. Typical switching energy losses as a function of gate resistor



Figure 14. Typical switching energy losses as a function of junction temperature

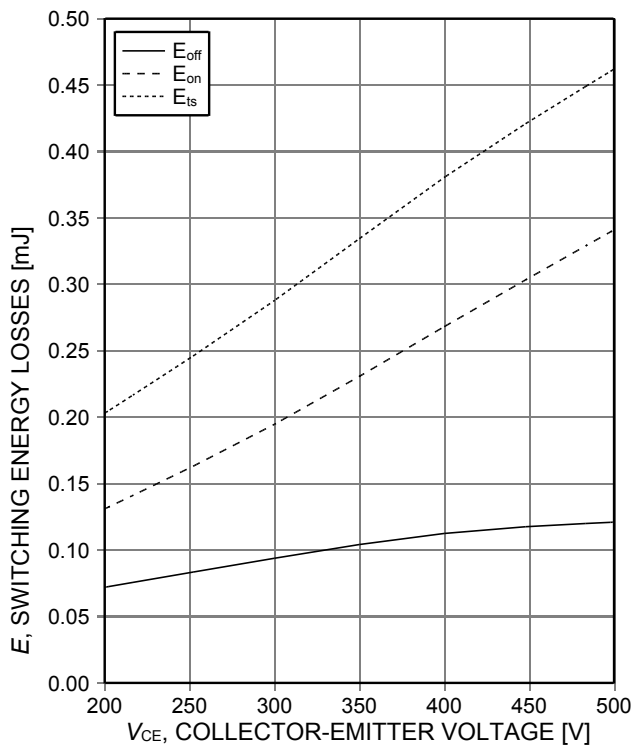


Figure 15. Typical switching energy losses as a function of collector emitter voltage

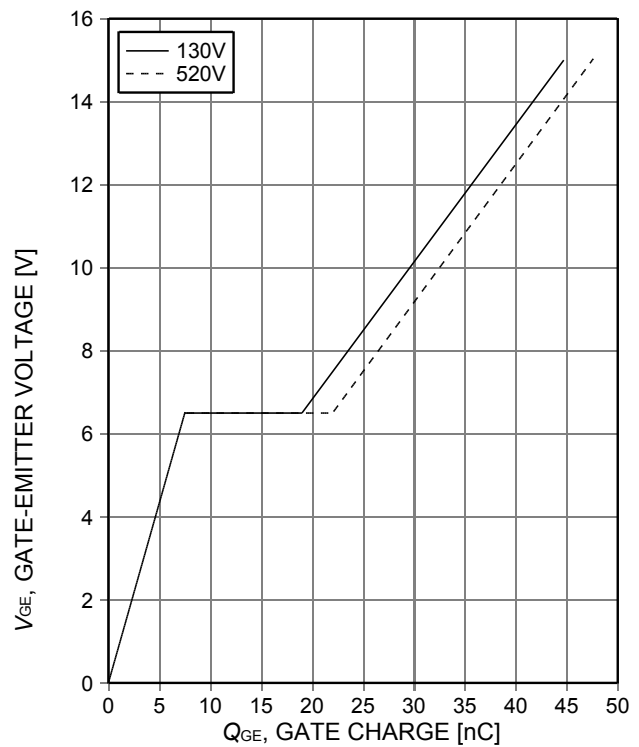


Figure 16. Typical gate charge

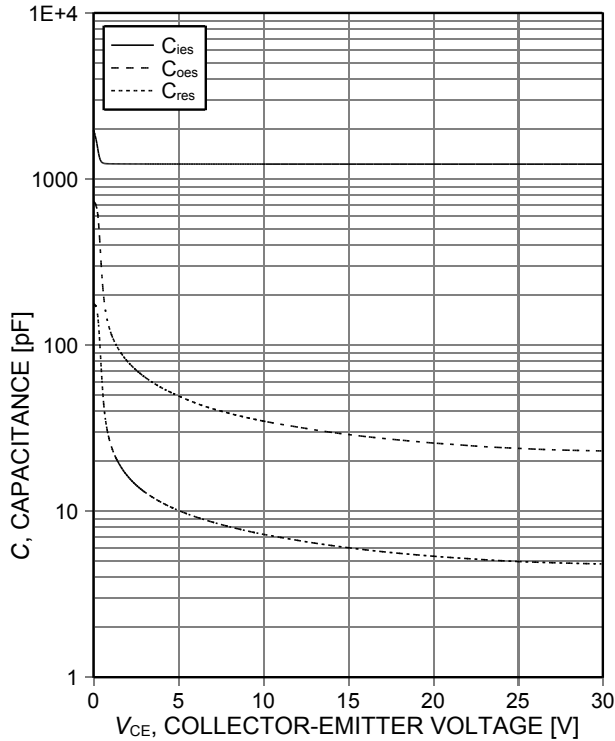


Figure 17. Typical capacitance as a function of collector-emitter voltage

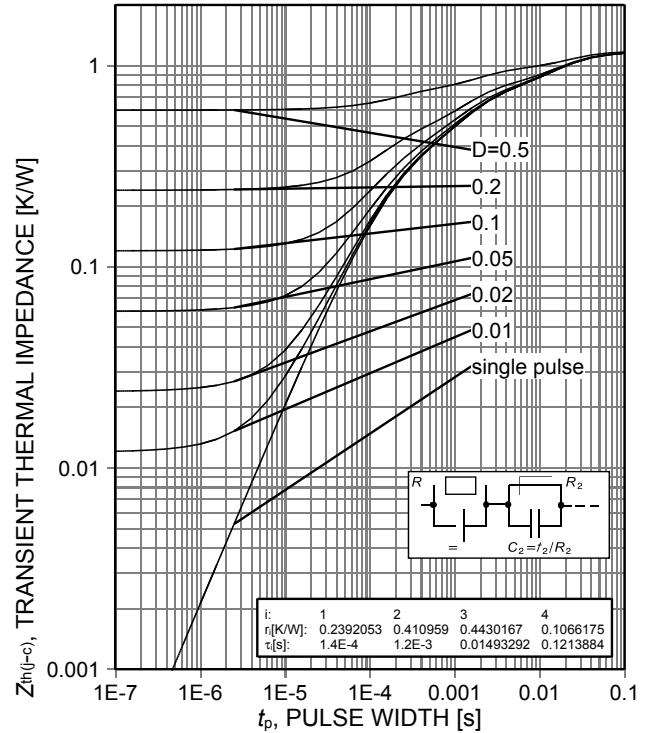


Figure 18. IGBT transient thermal impedance

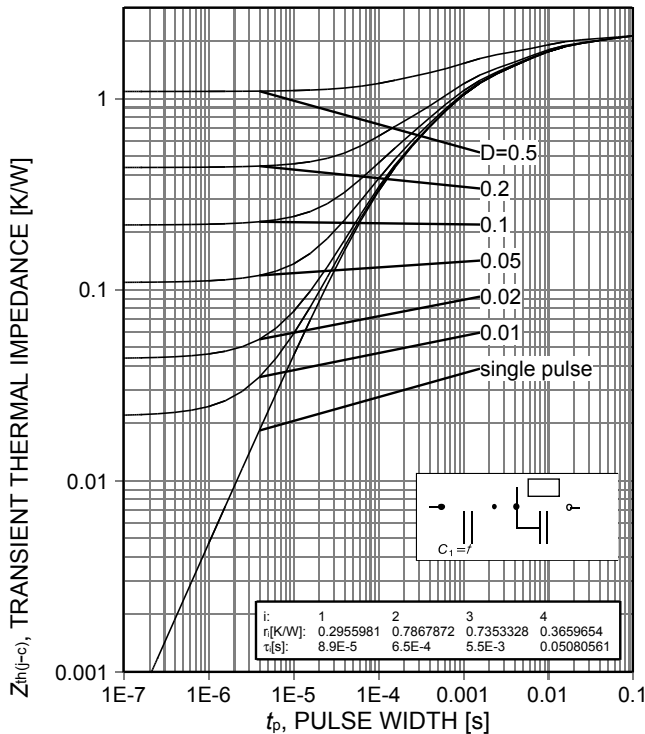


Figure 19. Diode transient thermal impedance as a function of pulse width

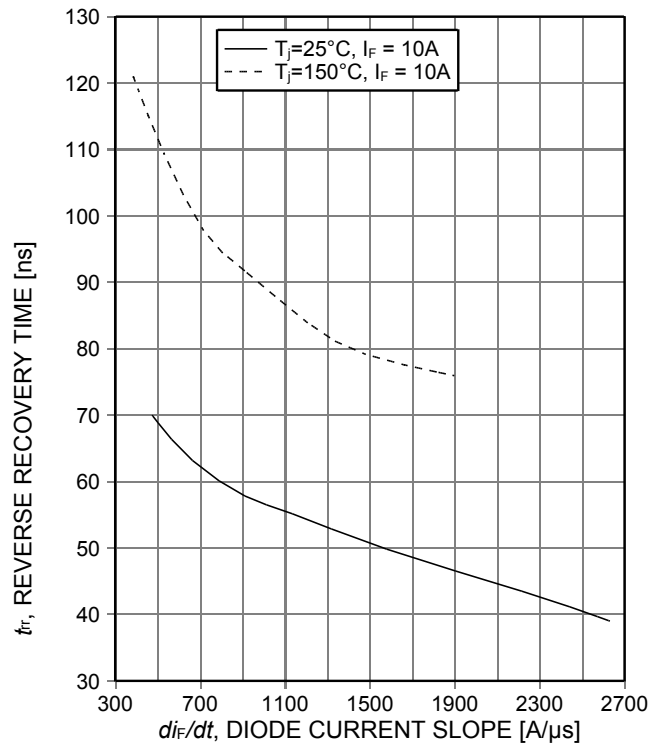
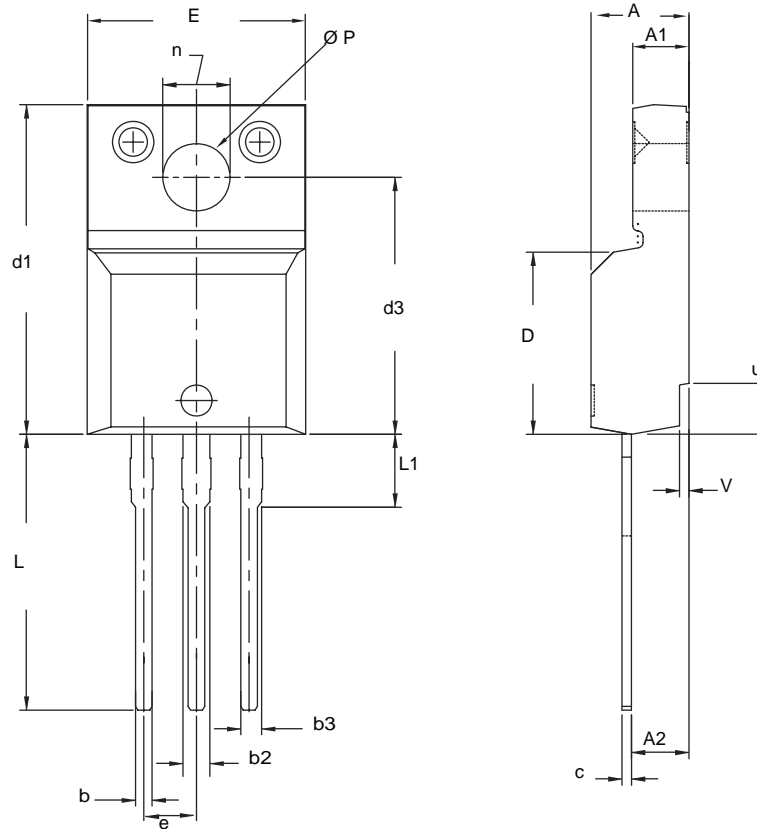


Figure 20. Typical reverse recovery time as a function of diode current slope

TO-220 FULLPAK (HIGH VOLTAGE)



DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.570	4.830	0.180	0.190
A1	2.570	2.830	0.101	0.111
A2	2.510	2.850	0.099	0.112
b	0.622	0.890	0.024	0.035
b2	1.229	1.400	0.048	0.055
b3	1.229	1.400	0.048	0.055
c	0.440	0.629	0.017	0.025
D	8.650	9.800	0.341	0.386
d1	15.88	16.120	0.622	0.635
d3	12.300	12.920	0.484	0.509
E	10.360	10.630	0.408	0.419
e	2.54 BSC		0.100 BSC	
L	13.200	13.730	0.520	0.541
L1	3.100	3.500	0.122	0.138
n	6.050	6.150	0.238	0.242
Ø P	3.050	3.450	0.120	0.136
u	2.400	2.500	0.094	0.098
v	0.400	0.500	0.016	0.020

Notes

1. To be used only for process drawing.
2. These dimensions apply to all TO-220, FULLPAK leadframe versions 3 leads.
3. All critical dimensions should C meet $C_{pk} > 1.33$.
4. All dimensions include burrs and plating thickness.
5. No chipping or package damage.

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